

16 GB DDR4 SDRAM SODIMM Specification

Specifications

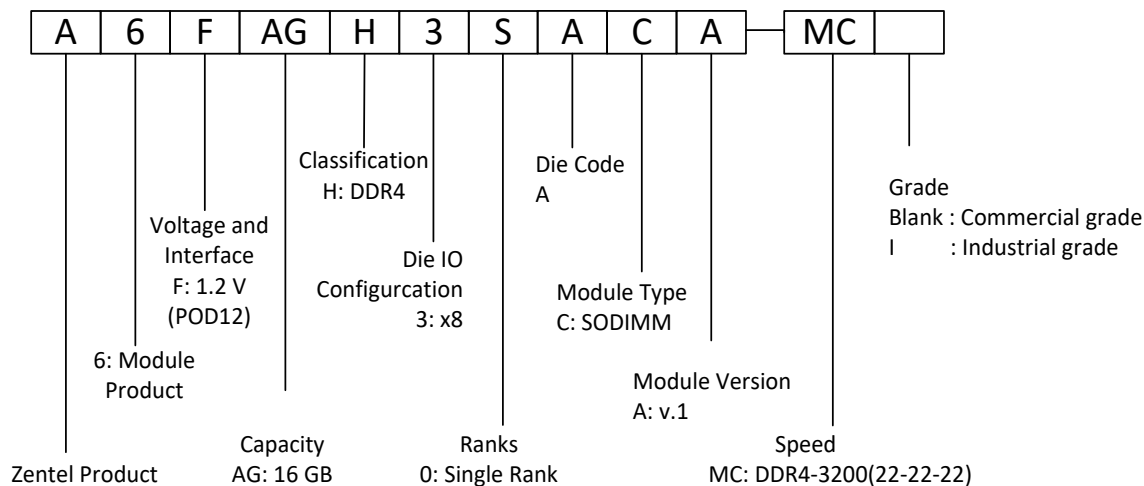
Max. Speed; CAS Latency	DDR4-3200@CL=22
Row Cycle Time (tRCmin)	45.75 ns
Row Active Time (tRASmin)	32 ns(min.)

Features

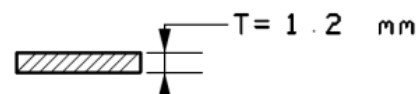
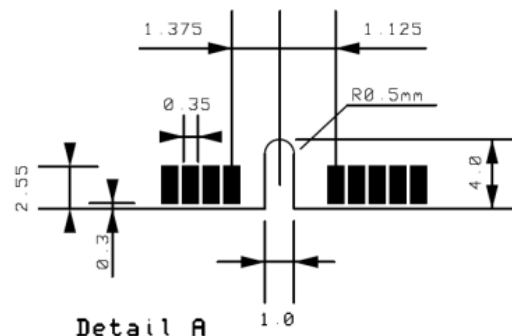
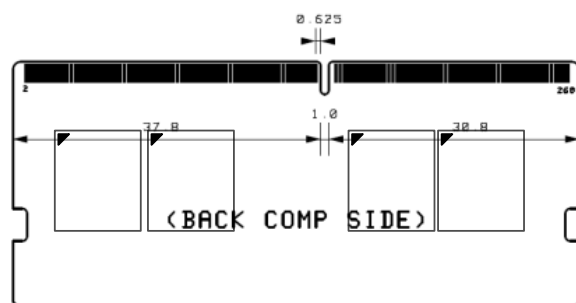
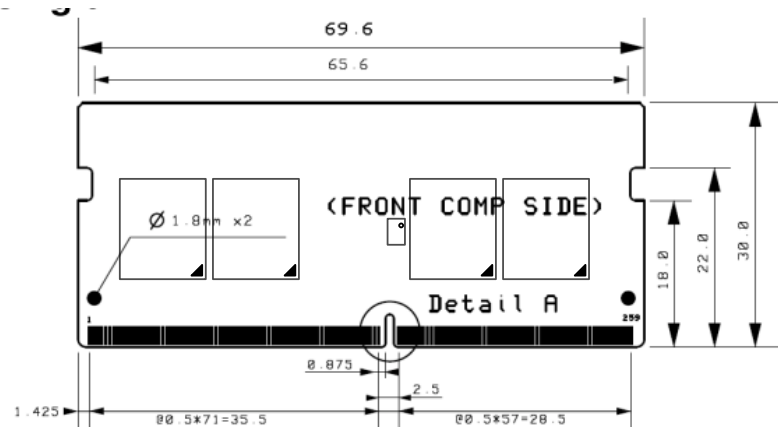
- 260-pin small outline dual in-line memory module (SODIMM)
- 1Rx8 memory module (1 rank of x8 DDR4 SDRAMs)
- Power supply:
 - VDD = VDDQ = 1.2V $\pm$ 5%
 - VPP = 2.5V -5%/+10%
 - VDDSPD = 2.2V to 3.6V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Low-power auto self refresh (LPASR)
- Data bus inversion (DBI) for data bus
- On-die VREFDQ generation and calibration
- On-board I²C serial presence-detect (SPD) EEPROM
- 16 internal banks; 4 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- Terminated control command and address bus
- PCB Height: 1.18" (30.00 mm)

1. Ordering Information

Part Number	Module Density	Configuration	Speed Bin (CL-nRCD-nRP)	Operating Temperature	Storage Temperature
A6FAGH3SACA-MC	16 GB	2G × 64 (2Gx8 1Rank)	DDR4-3200 (22-22-22)	0 °C to +85 °C	-55 °C to +100 °C
A6FAGH3SACA-MCI				-40 °C to +85 °C	-55 °C to +150 °C



Module Dimensions



TOLERANCE : $\pm 0.1 \text{ mm}$

UNIT : mm 03/05/20



Change History			
Doc. No.: DSA6FAGH3SACAF.(Rev.#)			
Rev. #	Who	When	What
01	Abby	2023-05-04	Initial version derived from DSA6FAGH3SACAZF.01; Updated header and footer